Elektronische Bauelemente

SSD3110-C

5.4A, 100V, $R_{DS(ON)}$ 310mΩ
N-Ch Enhancement Mode Power MOSFET

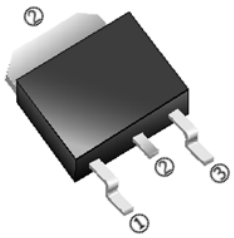
RoHS Compliant Product
A suffix of "-C" specifies halogen free

DESCRIPTION

SSD3110-C is the highest performance trench N-ch MOSFETs with extreme high cell density, which provides excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

SSD3110-C meets the RoHS and Green Product requirement with full function reliability approved.

TO-252(D-Pack)



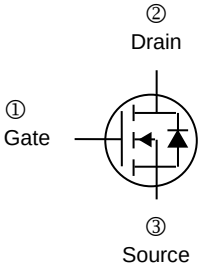
FEATURES

- Advanced High Cell Density Trench Technology
- Super Low Gate Charge
- Green Device Available

MARKING

PACKAGE INFORMATION

Package	MPQ	Leader Size
TO-252	2.5K	13 inch



ORDER INFORMATION

Part Number	Type
SSD3110-C	Lead (Pb)-free and Halogen-free

ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current @V_{GS}=10V [1]	T_C=25°C	I_D	5.4	A
	T_C=100°C		3.4	A
Pulsed Drain Current [2]		I_{DM}	11	A
Total Power Dissipation [3]	T_C=25°C	P_D	20.8	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C
Thermal Resistance Rating				
Thermal Resistance Junction-Ambient [1]		$R_{\theta JA}$	62	°C/W
Thermal Resistance Junction-Case [1]		$R_{\theta JC}$	6	

ELECTRICAL CHARACTERISTICS (T_J=25°C unless otherwise specified)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage		BV_{DSS}	100	-	-	V	V_{GS}=0, I_D=250μA
Gate-Threshold Voltage		$V_{GS(th)}$	1	-	2.5	V	V_{DS}=V_{GS}, I_D=250μA
Forward Transconductance		g_{fs}	-	5.4	-	S	V_{DS}=5V, I_D=3A
Gate-Source Leakage Current		I_{GSS}	-	-	±100	nA	V_{GS}= ±20V
Drain-Source Leakage Current	T_J=25°C	I_{DSS}	-	-	1	μA	V_{DS}=80V, V_{GS}=0
	T_J=55°C		-	-	5		
Static Drain-Source On-Resistance [2]		$R_{DS(ON)}$	-	-	310	mΩ	V_{GS}=10V, I_D=3A
			-	-	320		V_{GS}=4.5V, I_D=3A
Total Gate Charge		Q_g	-	9.6	-	nC	I_D=5A V_{DS}=80V V_{GS}=10V
Gate-Source Charge		Q_{gs}	-	1.83	-		
Gate-Drain (“Miller”) Change		Q_{gd}	-	1.85	-		
Turn-on Delay Time		$T_{d(on)}$	-	1.4	-	nS	V_{DD}=50V I_D=5A V_{GS}=10V R_G=3.3Ω
Rise Time		T_r	-	30.6	-		
Turn-off Delay Time		$T_{d(off)}$	-	11.2	-		
Fall Time		T_f	-	6	-		
Input Capacitance		C_{iss}	-	508	-	pF	V_{GS}=0 V_{DS}=15V f=1MHz
Output Capacitance		C_{oss}	-	29	-		
Reverse Transfer Capacitance		C_{rss}	-	16.4	-		
Source-Drain Diode							
Diode Forward Voltage [2]		V_{SD}	-	-	1.2	V	I_S=1A, V_{GS}=0, T_J=25°C
Reverse Recovery Time		T_{rr}	-	20	-	nS	I_F=5A, dI/dt=100A/μS, T_J=25°C
Reverse Recovery Charge		Q_{rr}	-	19	-	nC	
Continuous Source Current [1]		I_S	-	-	5.4	A	V_D=V_G=0, Force Current
Pulsed Source Current [2]		I_{SM}	-	-	11	A	

Notes:
1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2oz copper.
2. The data tested by pulsed , pulse width≦300μs, duty cycle≦2%.
3. The power dissipation is limited by 150°C, junction temperature.

CHARACTERISTIC CURVES

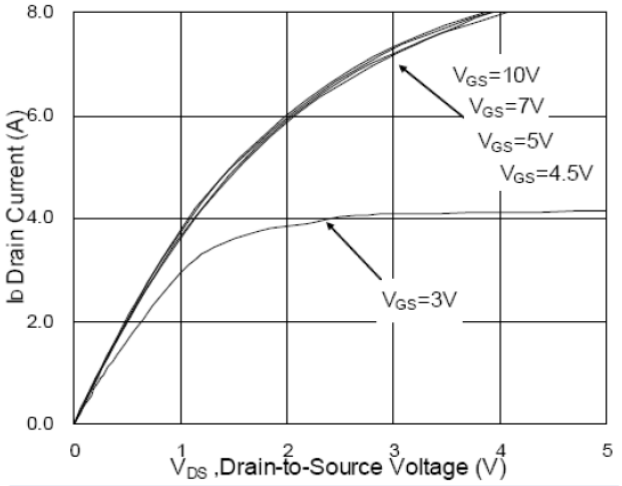


Fig.1 Typical Output Characteristics

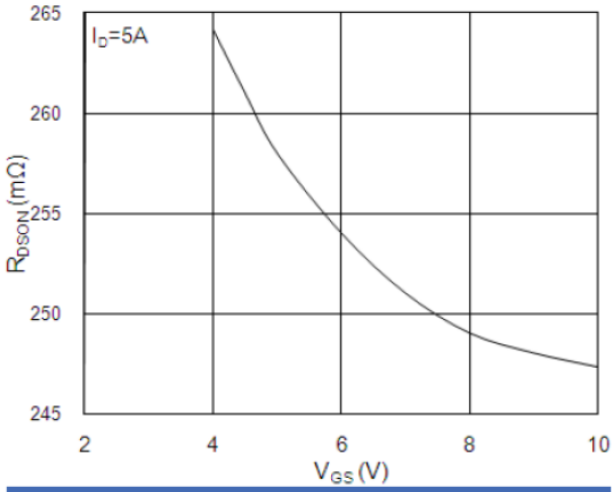


Fig.2 On-Resistance vs. Gate-Source

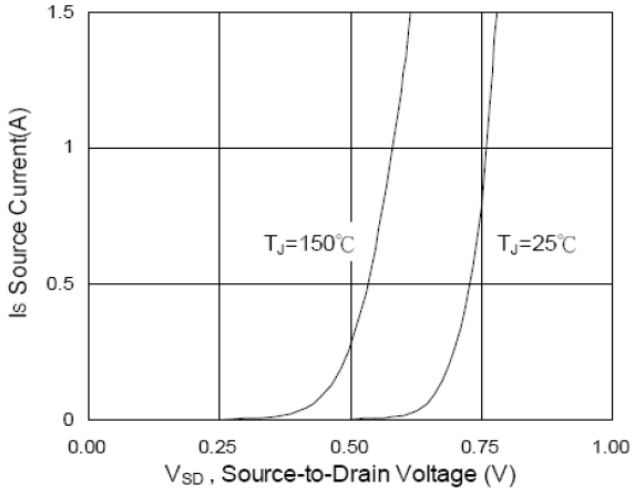


Fig.3 Forward Characteristics Of Reverse

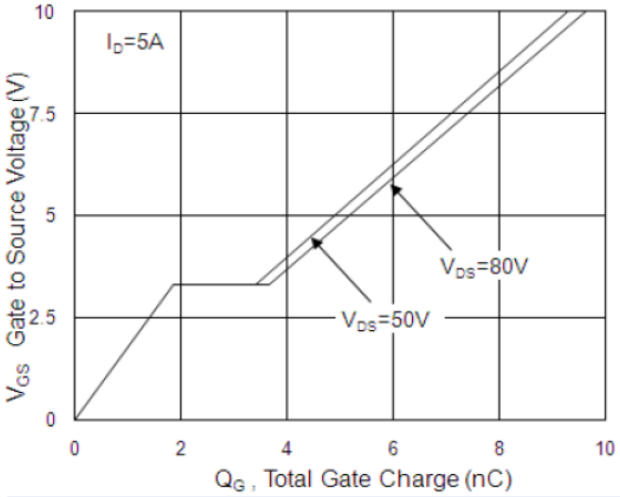


Fig.4 Gate-Charge Characteristics

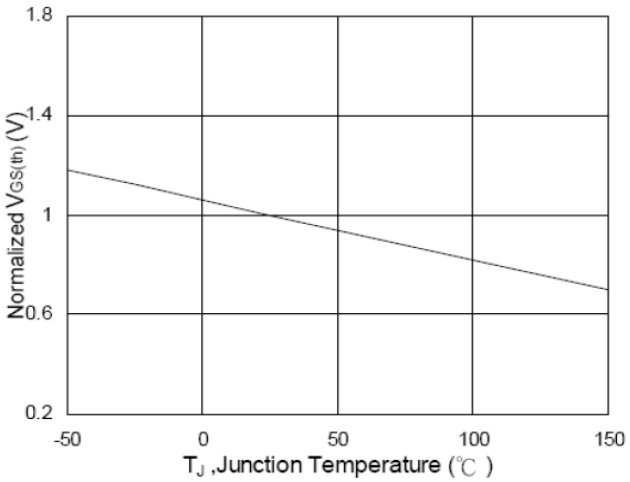


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

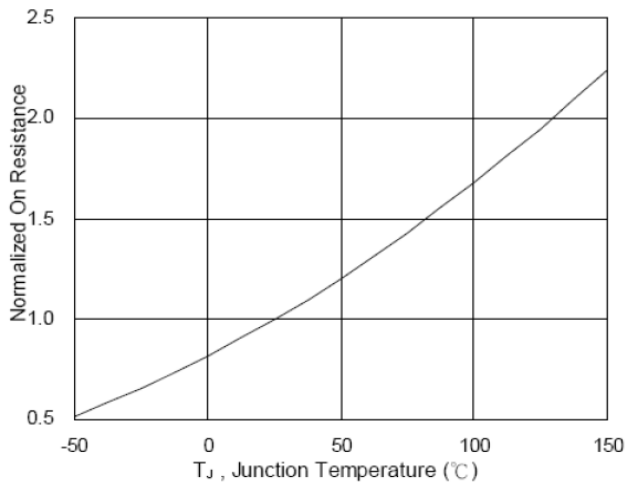


Fig.6 Normalized R_{DSON} vs. T_J

CHARACTERISTIC CURVES

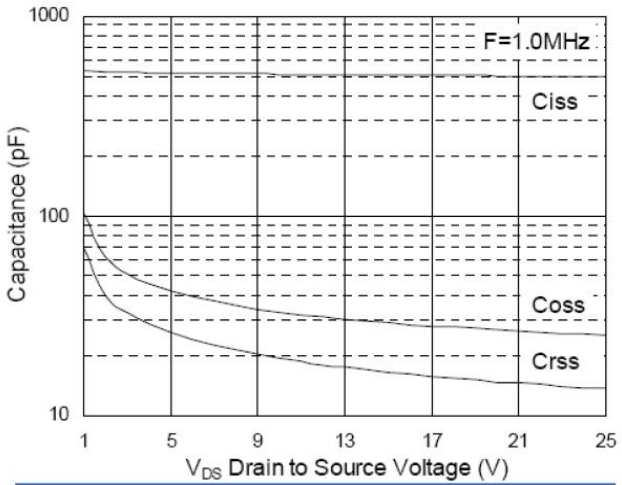


Fig.7 Capacitance

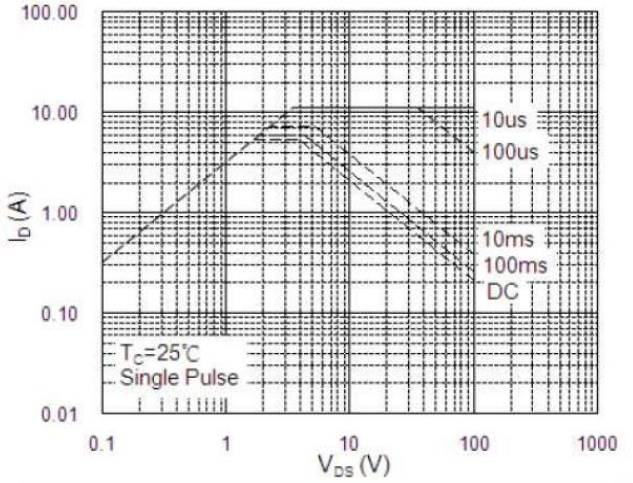


Fig.8 Safe Operating Area

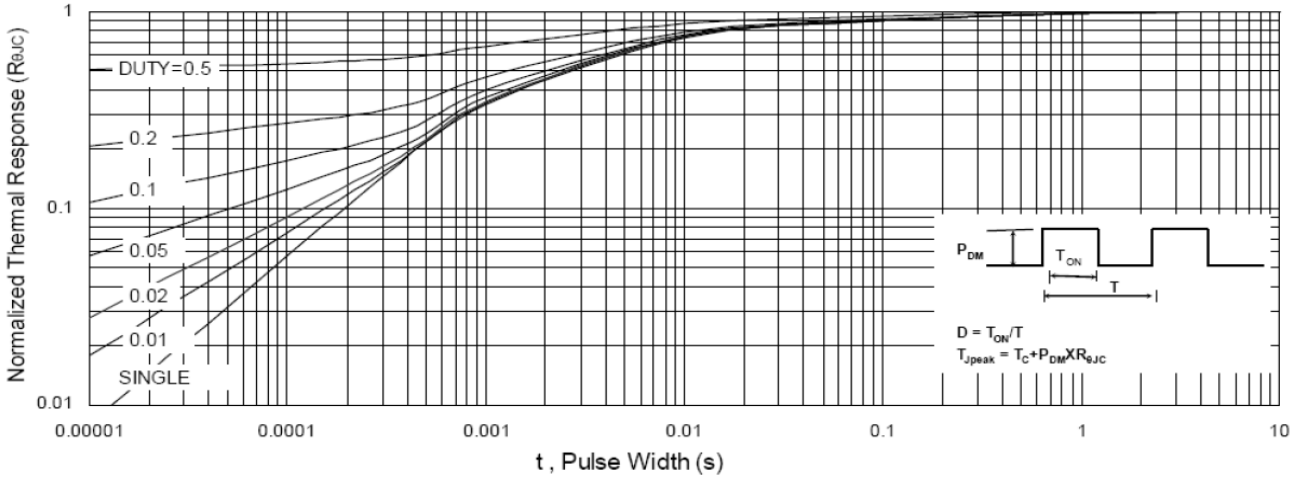


Fig.9 Normalized Maximum Transient Thermal Impedance

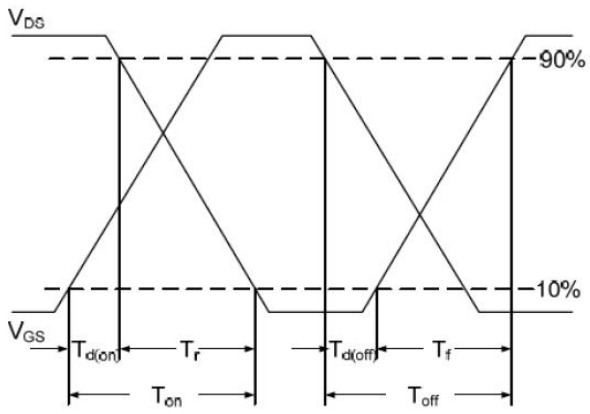


Fig.10 Switching Time Waveform

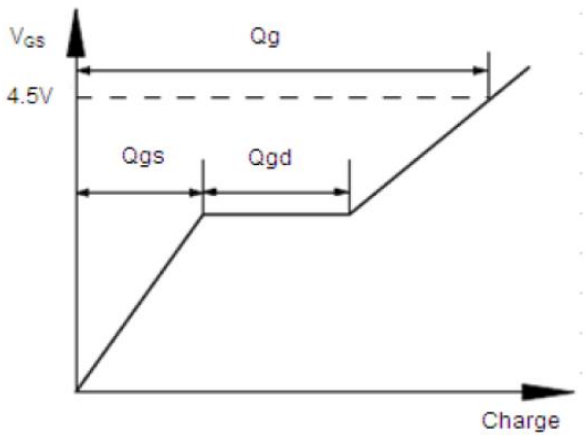
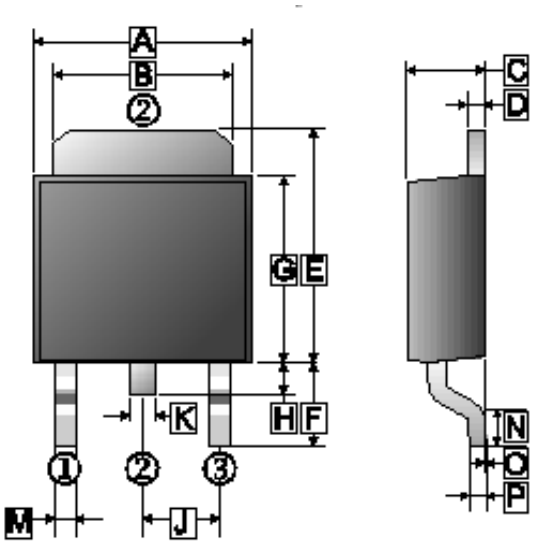


Fig.11 Gate Charge Waveform

PACKAGE OUTLINE DIMENSIONS

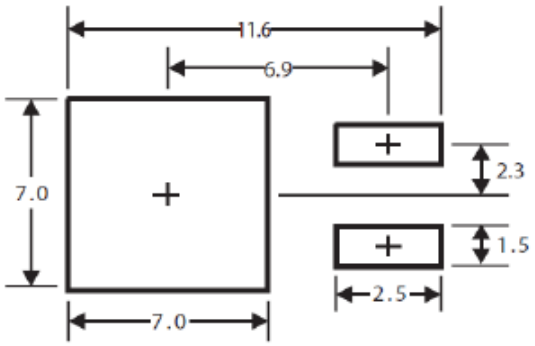
TO-252



REF.	Millimeter	
	Min.	Max.
A	6.30	6.90
B	4.95	5.53
C	2.10	2.50
D	0.40	0.90
E	6.00	7.70
F	2.90 REF.	
G	5.40	6.40
H	0.60	1.20
J	2.30 REF.	
K	0.89 REF.	
M	0.45	1.14
N	1.55 TYP.	
O	0	0.15
P	0.58 REF.	

MOUNTING PAD LAYOUT

TO-252



*Dimensions in millimeters